

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)
YPL-0026

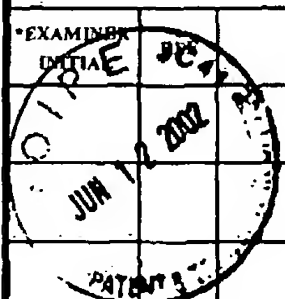
Application Number
10/086,496

Applicant(s)
GEUN-YOUNG YEOM, ET AL.

Filing Date
February 28, 2002

Group Art Unit

U.S. PATENT DOCUMENTS

*EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
						

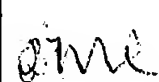
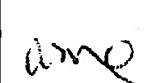
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FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

RECEIVED
AUG 21 2002
TC 1700

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	D.B. Oaks, W.G. Lawrence and A.H. Gelb, "Selective, Anisotropic and Damage-Free SiO ₂ Etching with a Hyperthermal Atomic Beam", Physical Sciences Inc., 20 New England Business Center, Andover, MA 01810, 7 pages
	M.J. Goeckner, T.K. Bennett, Jaeyoung Park, Z. Wang and S.A. Cohen, "Reduction of Residual Charge in Surface-Neutralization-Based Neutral Beams", 1997 2nd Int'l Symposium on Plasma Process-Induced Damage; May 13-14, pages 175-178

EXAMINER: 

DATE CONSIDERED
03-10-04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

